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BGA/CSP Development Update Service

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The third quarterly BGA/CSP update for 2002 features special coverage of the drivers for electronics manufacturing growth in China. A section on new IC package substrate developments is provided, including coverage of Phoenix Precision Technology's new flip chip production line and STI's substrate production in China and its new flip chip package. An analysis of new developments in wafer level testing is provided. New package developments such as stacked packages, bumpless flip die packages for memory devices, and LSI's introduction of wire bonding on active surface area are detailed.

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